

N-channel 80 V, 14 mΩ logic level MOSFET in LFPAK56 14 April 2016

Product data sheet

#### 1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

#### 2. **Features and benefits**

- Advanced TrenchMOS provides low R<sub>DSon</sub> and low gate charge •
- Logic level gate operation
- Avalanche rated, 100% tested •
- LFPAK provides maximum power density in a Power SO8 package

#### Applications 3.

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- Synchronous rectification in power supply equipment
- Chargers & adaptors with  $V_{out}$  < 10 V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

### 4. Quick reference data

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1.1.1

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	80	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	62	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	147	W
Static char	acteristics	· · · · · · · · · · · · · · · · · · ·		·		
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	12.2	15	mΩ
Dynamic cl	haracteristics			·		,
Q <sub>GD</sub>	gate-drain charge	$I_{D} = 15 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$ $T_{j} = 25 \text{ °C}; \overline{Fig. 13}; \overline{Fig. 14}$	-	8.7	-	nC

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UTA
4	G	gate	មុច្ចថ្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

### 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMN014-80YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN014-80YL	014L80

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

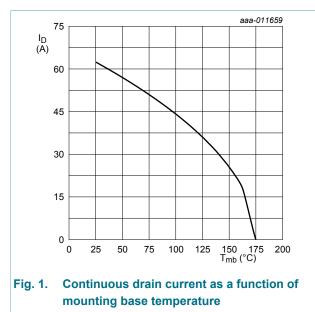
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	80	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ	-	80	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	147	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	62	А
		V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	-	44	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 4	-	250	А
T <sub>stg</sub>	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-drain	n diode					-
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	62	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	250	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{split} I_D &= 62 \text{ A};  \text{V}_{\text{sup}} \leq 80  \text{V};  \text{R}_{\text{GS}} = 50  \Omega; \\ \text{V}_{\text{GS}} &= 5  \text{V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. } 3 \end{split}$	[1][2]	-	79.6	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[2] Refer to application note AN10273 for further information.



V<sub>GS</sub>≥5V

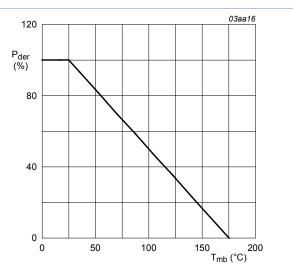
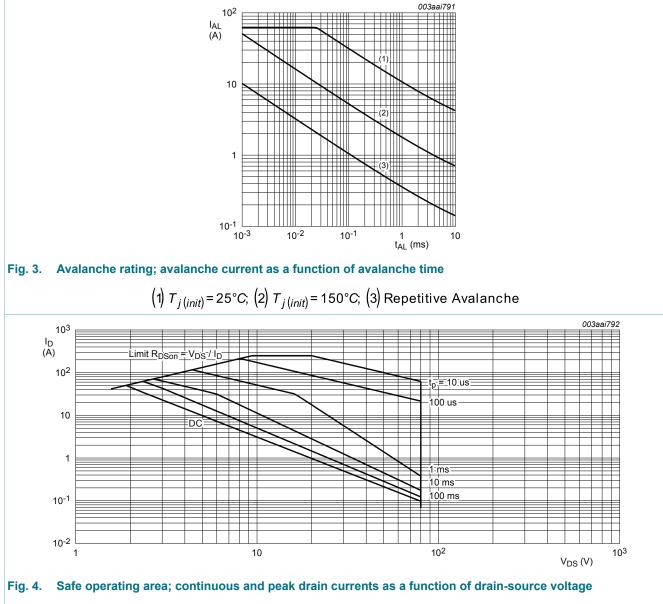


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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 $T_{mb}$  = 25°C;  $I_{DM}$  is a single pulse

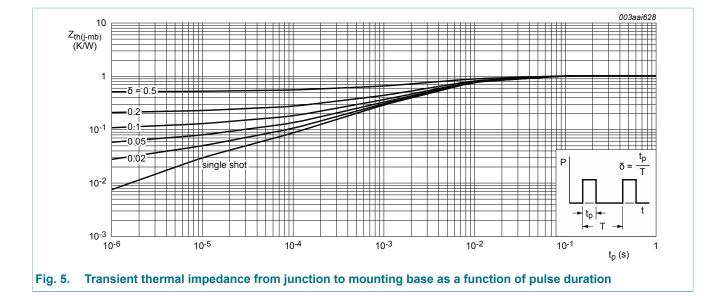
### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	1.02	K/W

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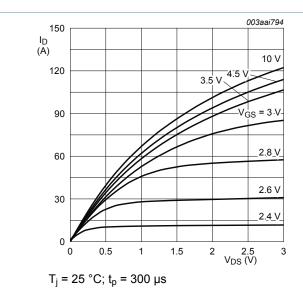
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics	· · · ·	I			
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	80	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	72	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <u>Fig. 9;</u> Fig. 10	1.4	1.7	2.1	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; Fig. 9$	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 80 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.25	10	μA
		V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	12.2	15	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 11	-	11.3	14	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	38	mΩ
Dynamic cł	naracteristics	· · · · ·				
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 15 A; $V_{DS}$ = 64 V; $V_{GS}$ = 5 V; T <sub>j</sub> = 25 °C; Fig. 13; Fig. 14	-	28.9	-	nC
		I <sub>D</sub> = 15 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 10 V; T <sub>i</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	56.9	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 5 V;	-	8.1	-	nC
Q <sub>GD</sub>	gate-drain charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	 -	8.7	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 25 V; $V_{GS}$ = 0 V; f = 1 MHz;	-	3479	4640	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u> $V_{DS} = 60 V; R_L = 4 Ω; V_{GS} = 5 V;$ $R_{G(ayt)} = 5 Ω; T_i = 25 °C$	 -	236	283	pF
C <sub>rss</sub>	reverse transfer capacitance		-	114	156	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 60 \text{ V}; \text{ R}_{L} = 4 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega; \text{ T}_{j} = 25 \text{ °C}$	-	15.3	-	ns
t <sub>r</sub>	rise time		-	24.6	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	45.3	-	ns
t <sub>f</sub>	fall time	-	-	24.7	-	ns
Source-dra	ain diode	1				
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 20 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	25.8	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C	-	29.3	-	nC





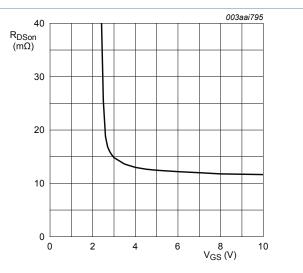


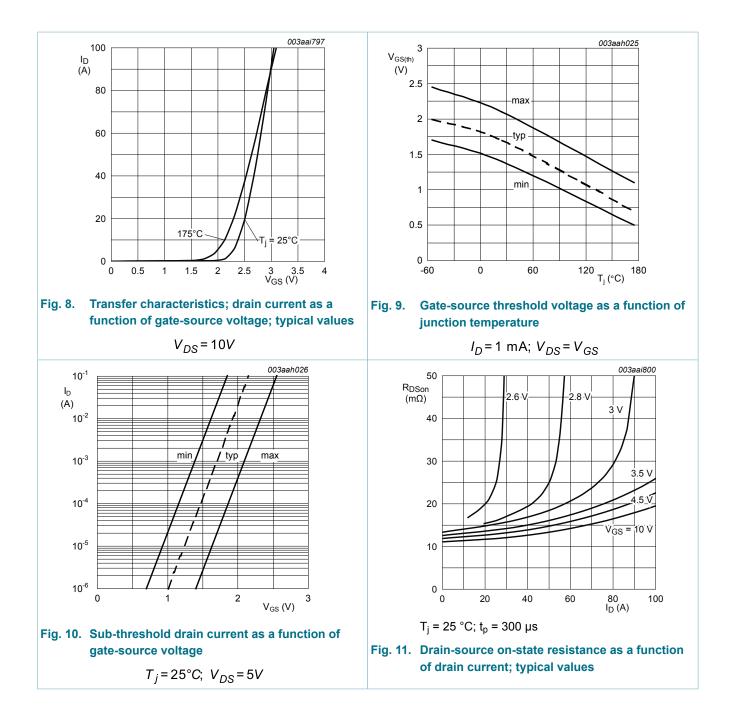
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 15A$ 

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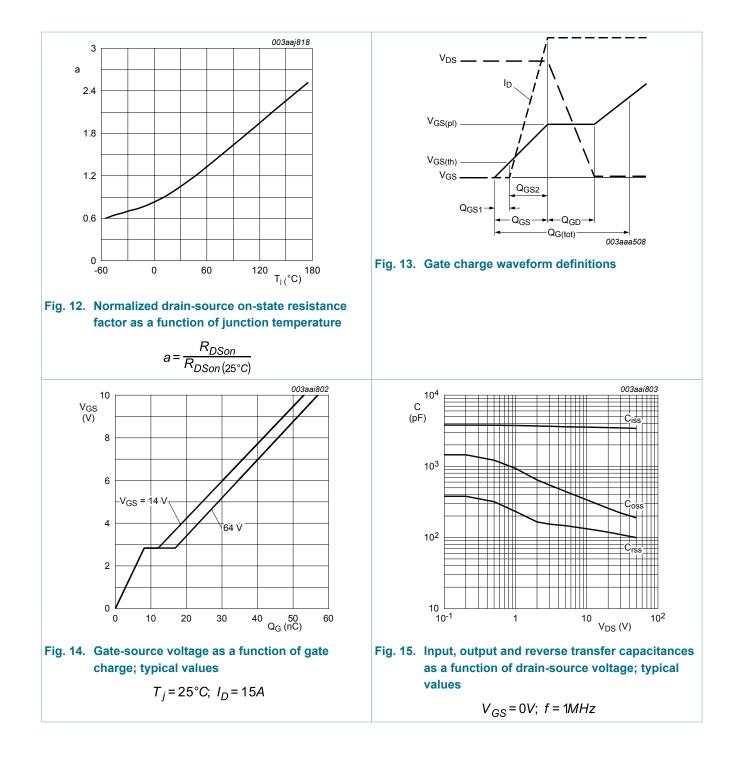
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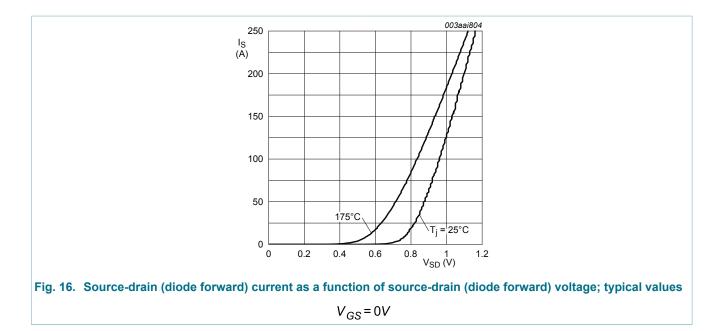
# PSMN014-80YL

#### N-channel 80 V, 14 m $\Omega$ logic level MOSFET in LFPAK56



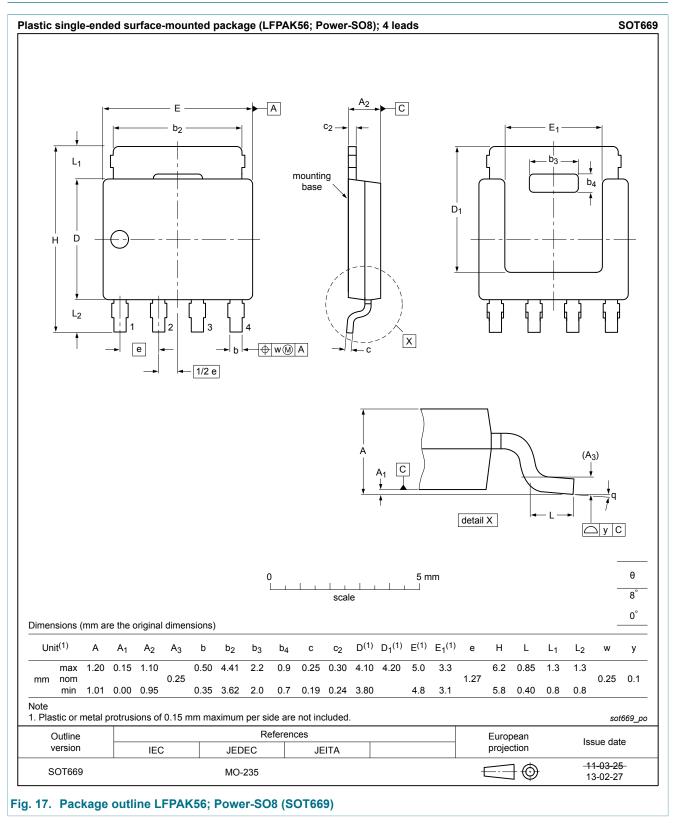
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#### N-channel 80 V, 14 m $\Omega$ logic level MOSFET in LFPAK56



N-channel 80 V, 14 m $\Omega$  logic level MOSFET in LFPAK56

### **11. Package outline**



PSMN014-80YL

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### 12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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